



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Phototransistor, side view type

RPM-22PB

The RPM-22PB is a silicon phototransistor in a side-facing package. High sensitivity with $\phi 1.5$ lens.

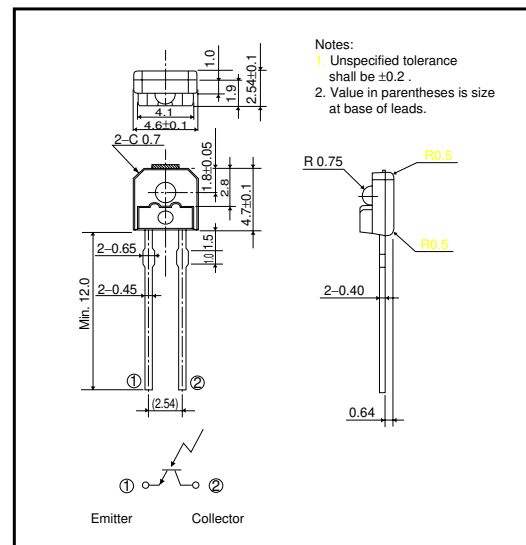
●Applications

Optical control equipment
Receiver for sensors

●Features

- 1) High sensitivity.
- 2) Molded in plastic with a visible light filter.
(Filter out light 750nm or less)
- 3) Side-facing detector.

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-emitter voltage	V_{CE0}	32	V
Emitter-collector voltage	V_{ECO}	5	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Operating temperature	T_{opr}	-25~+85	°C
Storage temperature	T_{stg}	-30~+100	°C

●Electrical and optical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Light current	I_C	0.48	-	1.94	mA	$V_{CE}=5V, E=500Lx$
Dark current	I_{CEO}	-	-	0.5	μA	$V_{CE}=10V$ (Black box)
Peak sensitivity wavelength	λ_P	-	800	-	nm	-
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	0.4	V	$I_C=0.1mA, E=500Lx$
Half-angle	$\theta_{1/2}$	-	± 32	-	deg	-
Response time	$t_r \cdot t_f$	-	10	-	μs	$V_{CE}=5V, I_C=1mA, R_L=100\Omega$

Sensors

●Electrical and optical characteristic curves

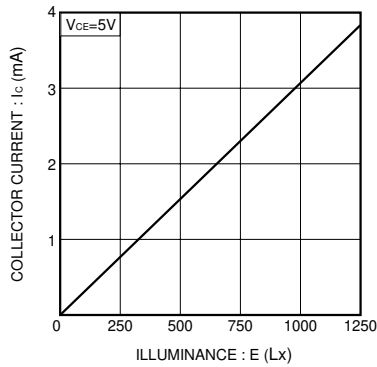


Fig.1 Collector current vs. emitting strength

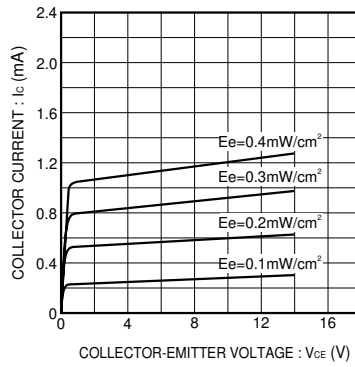


Fig.2 Output characteristics

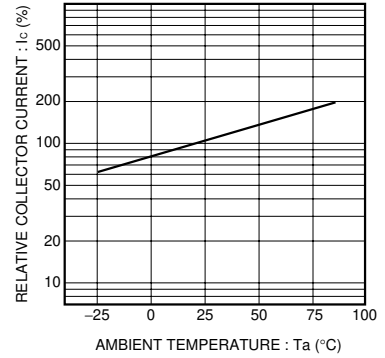


Fig.3 Relative output vs. ambient temperature

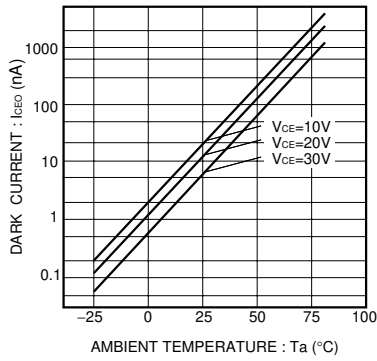


Fig.4 Dark current vs. ambient temperature

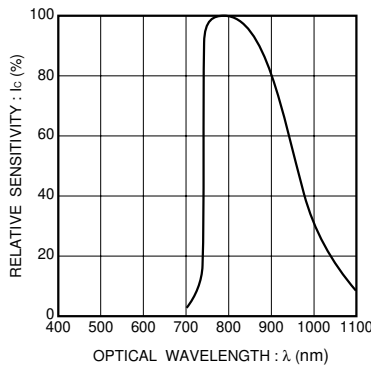


Fig.5 Spectral sensitivity

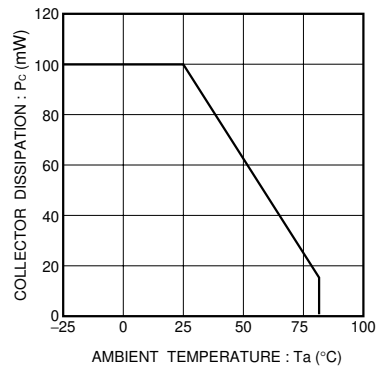


Fig.6 Collector dissipation vs. ambient temperature

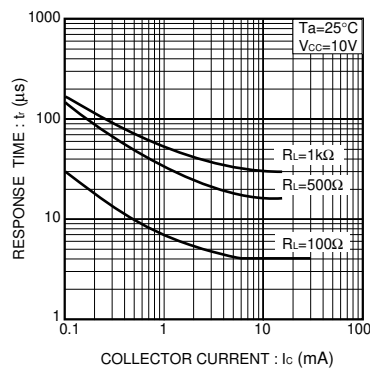


Fig.7 Response time vs. collector current

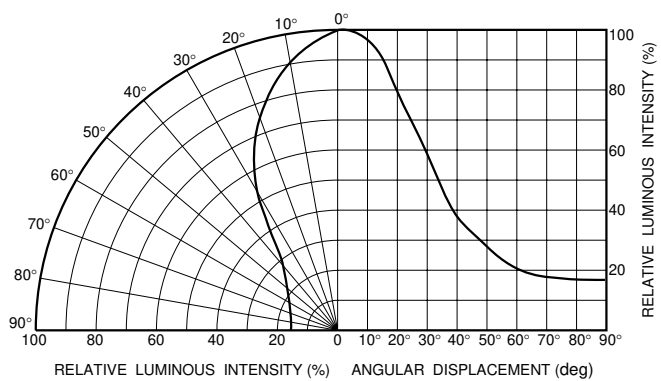


Fig.8 Directional pattern